

2SC4617 TRANSISTOR (NPN)

FEATURES

Power dissipation

$$P_{CM} : 0.15 \text{ W (Tamb=25}^\circ\text{C)}$$

Collector current

$$I_{CM} : 0.15 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : 60 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg}: -55^\circ\text{C to } +150^\circ\text{C}$$

SOT-523

1. BASE
2. EMITTER
3. COLLECTOR



ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=50 \mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=50 \mu\text{A}, I_C=0$	7			V
Collector cut-off current	I_{CBO}	$V_{CB}=60\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=7\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=6\text{V}, I_C=1\text{mA}$	120		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.4	V
Transition frequency	f_T	$V_{CE}=12\text{V}, I_C=2\text{mA}, f=100\text{MHz}$		180		MHz
Collector output capacitance	C_{ob}	$V_{CB}=12\text{V}, I_E=0, f=1\text{MHz}$			3.5	pF

CLASSIFICATION OF $h_{FE(1)}$

Rank	Q	R	S
Range	120-270	180-390	270-560
Marking	BQ	BR	BS